

SANYO

No.1789B

2SK545

N-Channel Junction Silicon FET

Impedance Converter Applications**Applications**

- Impedance converter applications.
- Infrared sensor.

Features

- Small I_{GSS} .
- Small C_{iss} .
- Ultracompact package permitting 2SK545-applied sets to be compact.

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

			unit
Drain-to-Source Voltage	V_{DSS}	40	V
Gate-to-Drain Voltage	V_{GDS}	-40	V
Gate Current	I_G	10	mA
Drain Current	I_D	1	mA
Power Dissipation	P_D	125	mW
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

Electrical Characteristics at $T_a = 25^\circ\text{C}$

			min	typ	max	unit
Gate-to-Drain Breakdown Voltage	$V_{(BR)GDS}$	$I_D = -10\mu\text{A}, V_{DS} = 0$	-40			V
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = -20\text{V}, V_{DS} = 0$			-500	pA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = 10\text{V}, I_D = 1\mu\text{A}$		-1.5	-4.0	V
Drain Current	I_{DSS}	$V_{DS} = 10\text{V}, V_{GS} = 0$	30※		300※	μA
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 10\text{V}, V_{GS} = 0, f = 1\text{kHz}$	0.05	0.13		mS
Input Capacitance	C_{iss}	$V_{DS} = 10\text{V}, V_{GS} = 0, f = 1\text{MHz}$		1.7		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = 10\text{V}, V_{GS} = 0, f = 1\text{MHz}$		0.7		pF

※ The 2SK545 is classified by I_{DSS} as follows (unit: μA):

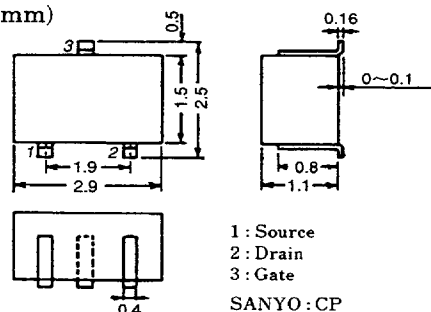
30	10	80	60	11	180	150	12	300
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(Note) Marking : B

I_{DSS} rank : 10, 11, 12

Package Dimensions 2050A

(unit: mm)

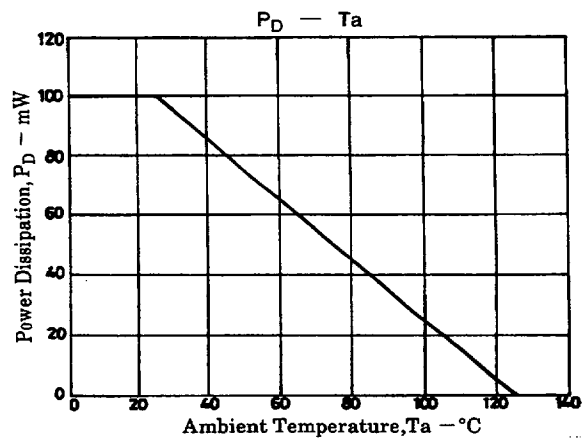
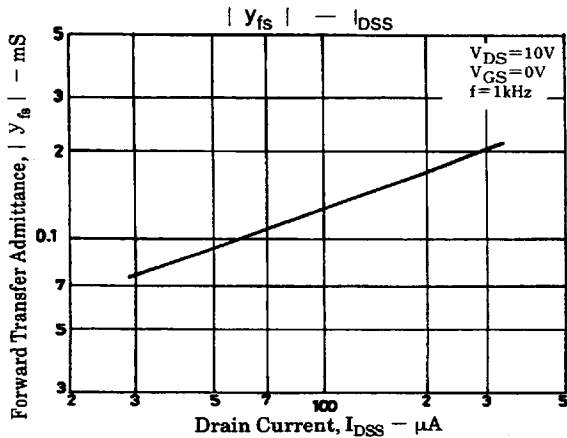
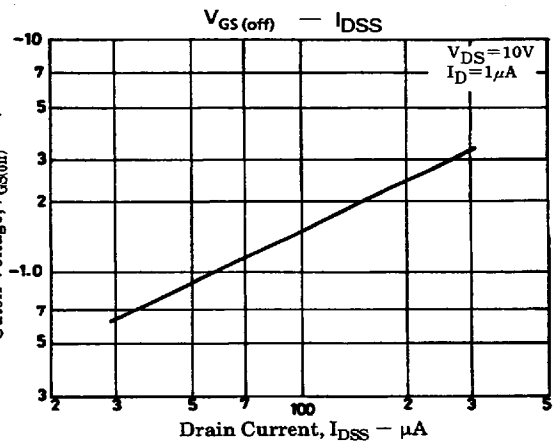
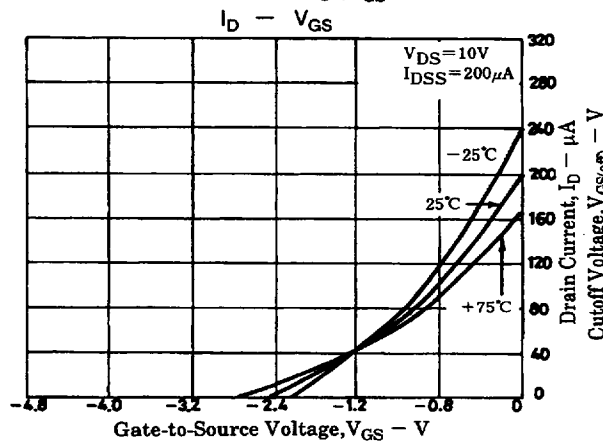
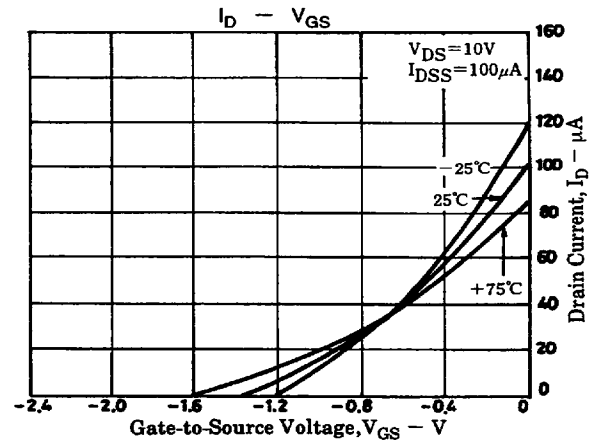
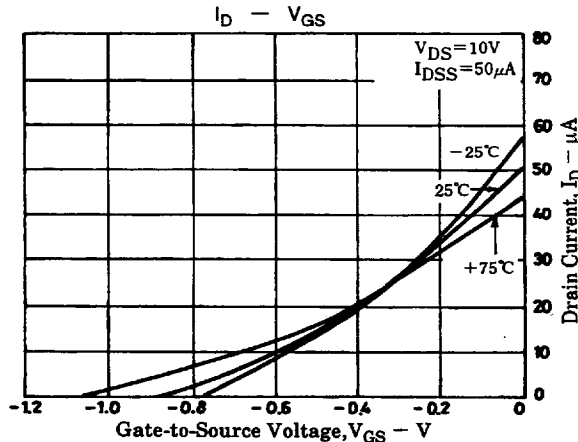
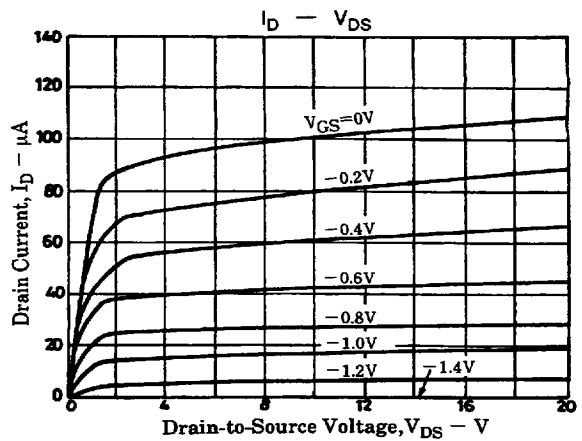
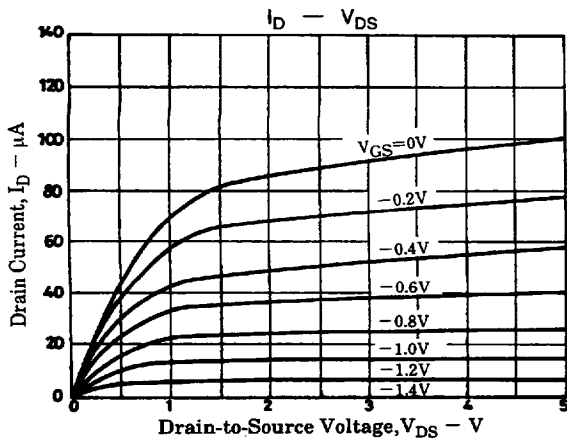


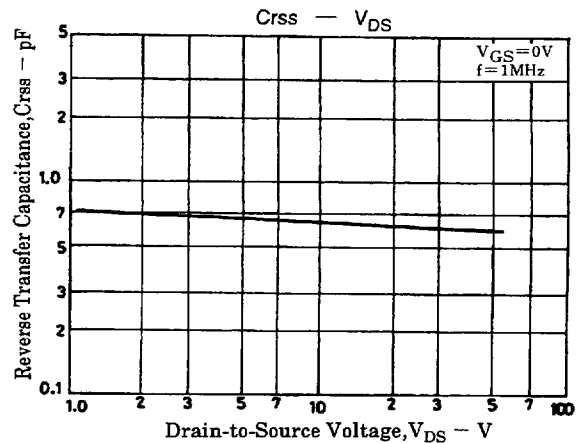
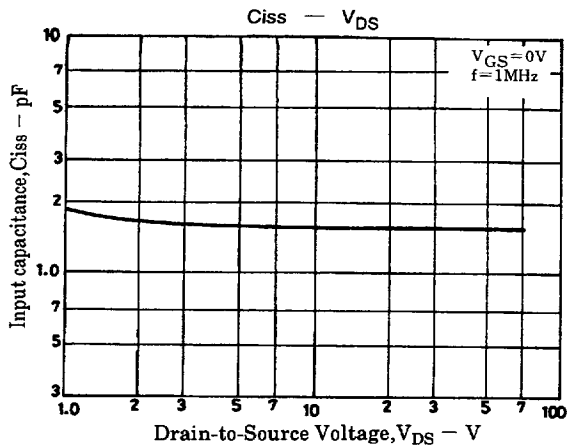
1: Source
2: Drain
3: Gate
SANYO: CP

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